Vishay Semiconductors



HEXFRED[®] Ultrafast Diodes, 300 A (INT-A-PAK Power Modules)



INT-A-PAK

PRIMARY CHARACTERISTICS					
V _R	1200 V				
V _F (typical) at 300 A at 25 °C	2.18 V				
t _{rr} (typical) at 45 A	233 ns				
I _{F(DC)} at T _C	300 A at 60 °C				
Package	INT-A-PAK				
Circuit configuration	Single diode				

FEATURES

- · Electrically isolated: DCB base plate
- Standard JEDEC[®] package
- · Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- Case style INT-A-PAK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

REMARKS

- Product reliability results valid for T_J = 150 °C
- Recommended operation temperature T_{op} = 150 °C

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Continuous forward current		T _C = 25 °C	375			
	IF	$T_{\rm C} = 60 \ ^{\circ}{\rm C}$	300	А		
Single pulse forward current	I _{FSM}	T _J = 25 °C	2400			
Maximum power dissipation	Р	T _C = 25 °C	1040	w		
	PD	$T_{\rm C} = 60 \ ^{\circ}{\rm C}$	750			
RMS isolation voltage	V _{ISOL}	50 Hz, circuit to base, all terminal shorted, t = 1 s	3500	V		
Junction temperature range	TJ		-40 to +150	°C		
Storage temperature range	T _{Stg}		-40 to +150	C		

ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 500 μA	1200	-	-		
Maximum forward voltage	V _{FM}	I _F = 300 A	-	2.18	2.23	V	
		I _F = 300 A, T _J = 150 °C	-	2.24	2.47		
Maximum reverse leakage current	I _{RM}	V _R = 1200 V	-	0.06	0.2	mA	
		T _J = 150 °C, V _R = 1200 V	-	-	20	III/A	

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Diode reverse recovery charge	Q _{rr}	T _J = 25 °C	I _F = 45 A V _R = 400 V dI _F /dt = 500 A/μs	-	3.5	-	μC
		T _J = 125 °C		-	10.4	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	233	-	- ns
		T _J = 125 °C		-	396	-	
Reverse recovery current	I _{rr}	T _J = 25 °C		-	30	-	A
		T _J = 125 °C		-	53	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum internal thermal r junction to case per leg	esistance,	R _{thJC}	DC operation	0.12	°C/W		
Typical thermal resistance, case to heatsink per modul	e	R _{thCS}	Mounting surface flat, smooth, and greased	0.05			
	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.	4			
Mounting torque ± 10 % busba	busbar			6	Nm		
Approximate weight				200	g		
Approximate weight			7.1	oz.			
Case style				INT-A-PAK			



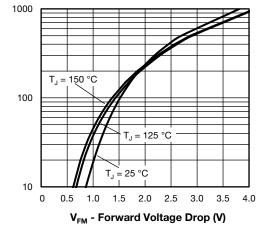


Fig. 1 - Typical Forward Voltage Drop Characteristics

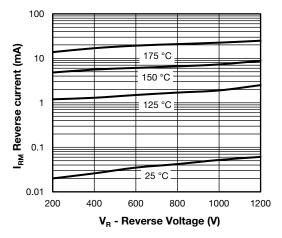


Fig. 2 - Typical Value of Reverse Current vs. Reverse Voltage



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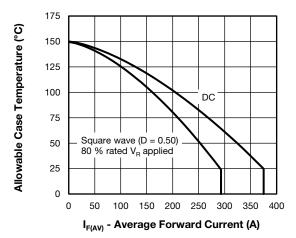


Fig. 3 - Maximum Allowable Case Temperature vs. Average Forward Current

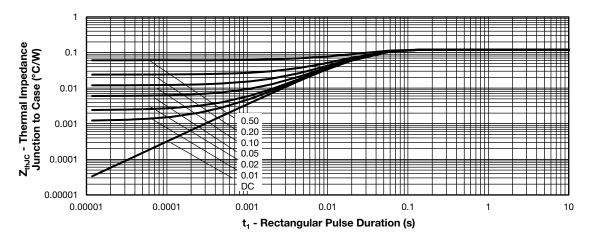


Fig. 4 - Maximum Thermal Impedance RthJC Characteristics

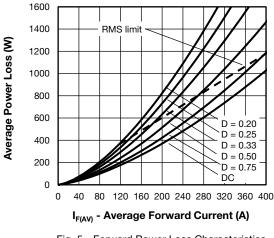


Fig. 5 - Forward Power Loss Characteristics

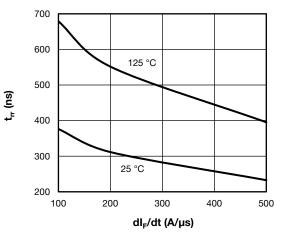


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

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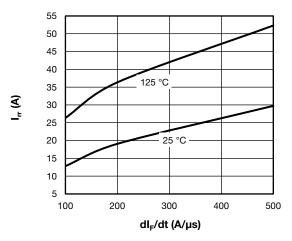
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12300 10300 125 °C 8300 Q_{rr} (nC) 6300 4300 25 °C 2300 300 200 300 400 500 100 dl_F/dt (A/µs)

Fig. 7 - Typical Reverse Recovery Charge vs. dl_F/dt

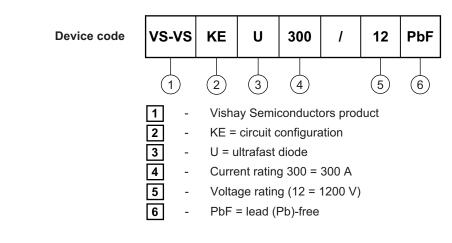


VS-VSKEU300/12PbF

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Fig. 8 - Typical Reverse Recovery Current vs. dl_F/dt

ORDERING INFORMATION TABLE



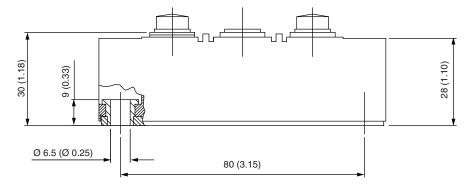
CIRCUIT CONFIGURATION

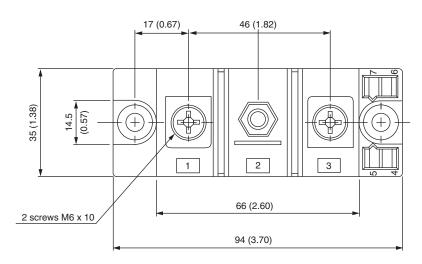


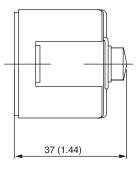


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DIMENSIONS in (inches) millimeters INT-A-PAK DBC







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